

DDTA (R1 = R2 SERIES) UA

PNP PRE-BIASED SMALL SIGNAL SOT-323
SURFACE MOUNT TRANSISTOR

Features

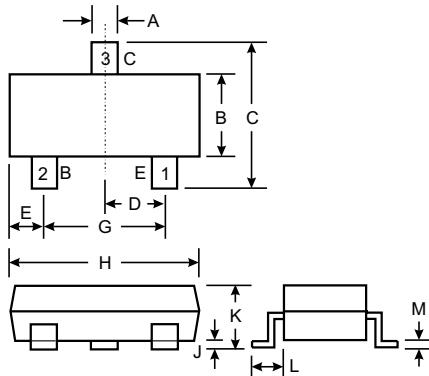
- Epitaxial Planar Die Construction
- Complementary NPN Types Available (DDTC)
- Built-In Biasing Resistors, R1 = R2

Mechanical Data

- Case: SOT-323, Molded Plastic
- Case material - UL Flammability Rating 94V-0
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approx.)

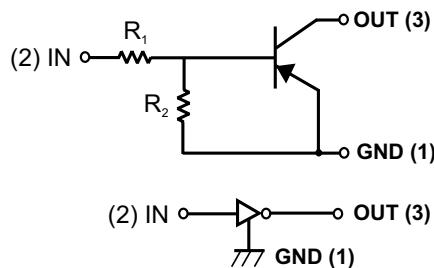
P/N	R1, R2 (NOM)	MARKING
DDTA123EUA	2.2K	P04
DDTA143EUA	4.7K	P08
DDTA114EUA	10K	P13
DDTA124EUA	22K	P17
DDTA144EUA	47K	P20
DDTA115EUA	100K	P24

UNDER DEVELOPMENT



SOT-323		
Dim	Min	Max
A	0.37	0.51
B	1.19	1.40
C	2.10	2.50
D	0.89	1.05
E	0.45	0.61
G	1.78	2.05
H	2.65	3.05
J	0.013	0.15
K	0.89	1.10
L	0.45	0.61
M	0.076	0.178

All Dimensions in mm



SCHEMATIC DIAGRAM

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage, (3) to (1)	V_{CC}	-50	V
Input Voltage, (2) to (1)	V_{IN}	+10 to -12 +10 to -30 +10 to -40 +10 to -40 +10 to -40 +10 to -40	V
Output Current	I_O	50	mA
Output Current	I_O	-100 -100 -50 -30 -30 -20	mA
Output Current	I_C (Max)	-100	mA
Power Dissipation	P_d	200	mW
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	°C

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	$V_{I(\text{off})}$	—	-0.5	-1.1	—	V	$V_{CC} = 5\text{V}$, $I_O = 100\mu\text{A}$
	$V_{I(\text{on})}$	—	—	-1.9	-3		$V_O = 0.3\text{V}$, $I_O = 20\text{mA}$, DDTA123EUA $V_O = 0.3\text{V}$, $I_O = 20\text{mA}$, DDTA143EUA $V_O = 0.3\text{V}$, $I_O = 10\text{mA}$, DDTA114EUA $V_O = 0.3\text{V}$, $I_O = 5\text{mA}$, DDTA124EUA $V_O = 0.3\text{V}$, $I_O = 2\text{mA}$, DDTA144EUA $V_O = 0.3\text{V}$, $I_O = 1\text{mA}$, DDTA115EUA
Output Voltage	$V_{O(\text{on})}$	—	—	-0.1	-0.3	V	$I_O/I_I = 10\text{mA}/0.5\text{mA}$, DDTA123EUA $I_O/I_I = 10\text{mA}/0.5\text{mA}$, DDTA143EUA $I_O/I_I = 10\text{mA}/0.5\text{mA}$, DDTA114EUA $I_O/I_I = 10\text{mA}/0.5\text{mA}$, DDTA124EUA $I_O/I_I = 10\text{mA}/0.5\text{mA}$, DDTA144EUA $I_O/I_I = 5\text{mA}/0.25\text{mA}$, DDTA115EUA
Input Current	DDTA123EUA DDTA143EUA DDTA114EUA DDTA124EUA DDTA144EUA DDTA115EUA	I_I	—	—	-3.8 -1.8 .88 .36 .18 .15	mA	$V_I = -5\text{V}$
Output Current	$I_{O(\text{off})}$	—	—	0.5	μA	$V_{CC} = -50\text{V}$, $V_I = 0\text{V}$	
DC Current Gain	DDTA123EUA DDTA143EUA DDTA114EUA DDTA124EUA DDTA144EUA DDTA115EUA	G_I	-20 -20 -30 -56 -68 -82	—	—	—	$V_O = -5\text{V}$, $I_O = -20\text{mA}$ $V_O = -5\text{V}$, $I_O = -10\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$ $V_O = -5\text{V}$, $I_O = -5\text{mA}$
Resistance Ratio	R_2/R_1	0.8	1	1.2	—	—	—
Gain-Bandwidth Product*	f_T	—	250	—	MHz	$V_{CE} = -10\text{V}$, $I_E = 5\text{mA}$, $f = 100\text{MHz}$	

* Transistor - For Reference Only

UNDER DEVELOPMENT